

## **NCE N-Channel Super Trench II Power MOSFET**

#### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

## **Application**

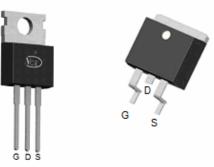
- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

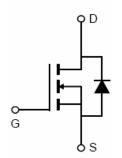
#### **General Features**

- $V_{DS}$  =100V, $I_D$  =200A  $R_{DS(ON)}$ =2.4m $\Omega$  , typical (TO-220)@  $V_{GS}$ =10V  $R_{DS(ON)}$ =2.2m $\Omega$  , typical (TO-263)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP026N10	NCEP026N10	TO-220	-	-	-
NCEP026N10D	NCEP026N10D	TO-263	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	200	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	142	Α
Pulsed Drain Current	I <sub>DM</sub>	800	Α
Maximum Power Dissipation	P <sub>D</sub>	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	2300	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}$ C



# NCEP026N10, NCEP026N10D

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>eJC</sub>	0.5	°C/W	
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

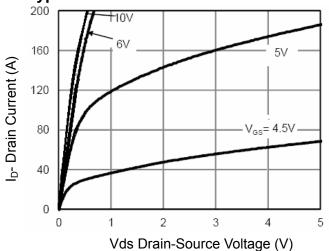
Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA		100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>G</sub>	<sub>S</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{D}$	<sub>S</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	50µA	2.0	3.0	4.0	V
Drain Course On State Besietenes	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =100A	TO-220	-	2.4	2.6	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		TO-263		2.2	2.6	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =1	00A		90	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V, F=1.0MHz		-	14000	-	PF
Output Capacitance	Coss			-	1100	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	60	-	PF
Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>			-	34	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50V, $I_{D}$ =100A $V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$		-	27	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>			-	78	-	nS
Turn-Off Fall Time	t <sub>f</sub>			-	30	-	nS
Total Gate Charge	Qg	\/ -50\/   -4	1004	-	240	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =50V,I <sub>D</sub> =100A, V <sub>GS</sub> =10V		-	62		nC
Gate-Drain Charge	$Q_{gd}$			-	73		nC
Drain-Source Diode Characteristics	<u> </u>					'	
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =100A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	200	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> =	100A	-	101	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>		-	280	-	nC

#### Notes:

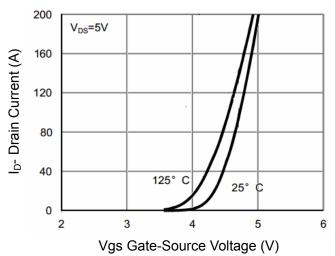
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V  $_{\text{DD}}$  =50 V,V  $_{\text{G}}$  =10 V,L=0.5 mH,Rg=25  $\Omega$



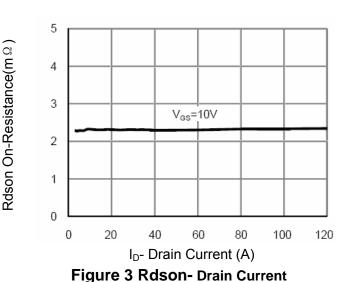




**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 



2 Normalized On-Resistance 1.8 V<sub>GS</sub>=10V I<sub>D</sub>=100 A 1.6 1.4 1.2 8.0 25 50 75 100 125 150 175 T<sub>J</sub>-Junction Temperature(°C)

**Figure 4 Rdson-Junction Temperature** 

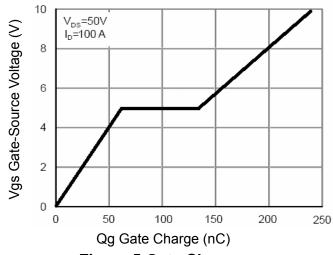


Figure 5 Gate Charge

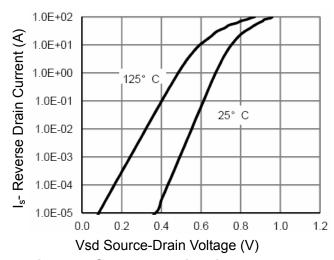


Figure 6 Source- Drain Diode Forward



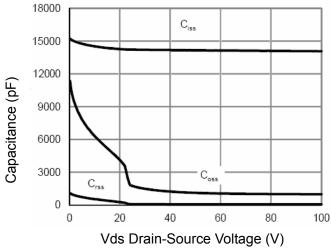


Figure 7 Capacitance vs Vds

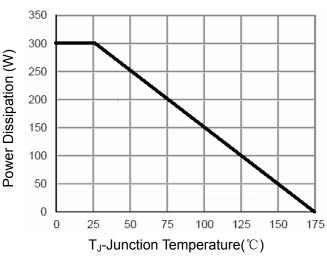
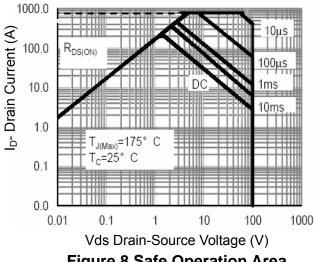


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

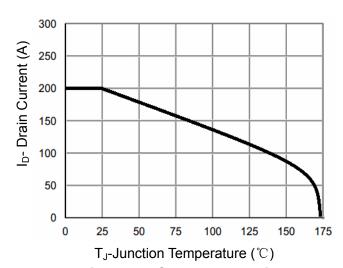


Figure 10 Current De-rating

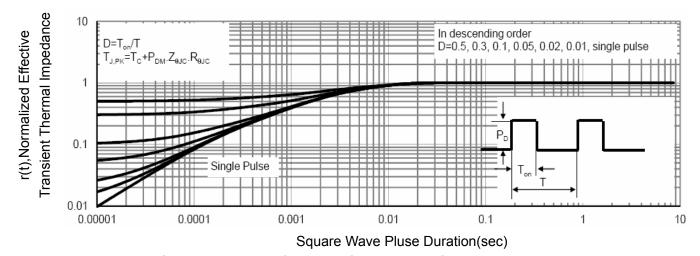
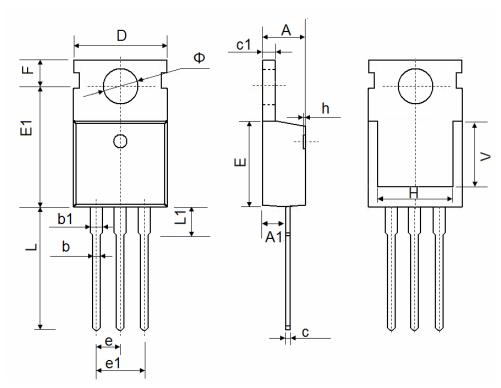


Figure 11 Normalized Maximum Transient Thermal Impedance



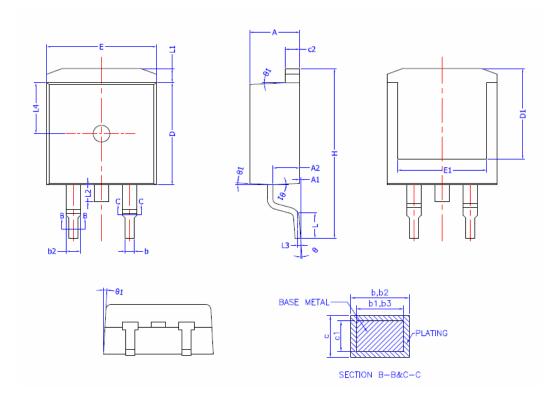
# **TO-220-3L Package Information**



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	6.900 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



# **TO-263-2L Package Information**



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76	_	0,89	
b1	0,75	0,80	0,85	
b2	1,23		1,37	
b3	1,22	1,27	1,32	
С	0,47	_	0,60	
c1	0.46	0,51	0.56	
c2	1,25	1,30	1,35	
D	9.10	9,20	9.30	
D1	8,00	—	—	
E	9.80	9.90	10.00	
E1	7.80	_	_	
е	2.	54 BSC		
Н	14.90	15.30	15.70	
L	2.00	2,30	2.60	
L1	1.17	1.27	1.40	
L2	_	_	1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	_	8°	
θ1	1°	3°	5°	

# 新加車CEPOWER

# NCEP026N10, NCEP026N10D

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